FORM PTO-1449

			Sheet 1 of 1
FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE (Rev. 2-32) PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. F1S9-1997-0266US4	SERIAL NO To Be Assigned	5 5
Information Disclosure Statement by Applicant	APPLICANT Wang et al.		87414 87414
(Use several sheets if necessary)	FILING DATE Herewith	GRÓUP	001F

U.S. PATENT DOCUMENTS

Exmr Initial	Document Number	Date	Name	Class	Sub Class	Filin Date
0~/	5,047,367	09/10/91	Wei et al	437	200	Date
ON	5,094,981	03/10/92	Chung et al.	437	190	
ON	5,250,467	10/05/93	Somekh et al.	438	192	
0~	5,302,552	04/12/94	Duchateau et al.	438	664	
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Exmr Initial		Document Number	Date		Country		Class	Sub Class		station NO
11/1	JP	7-321069	12-08-95	Japan				-	1	T
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OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

(1)	IBM Docket No. BU9-93-016V entitled Low Temperature Formation of Low Resistivity Titanium Silicide, now
	USPTO S/N 08/586,046, filed 01/16/96. See application as filed, pages 1-26, with disclosure BU8-95-0143,
	Pages 1-18, w/Figures 1-7 on 5 pages of drawings.
	(1)

Examiner	0 ~	Date Considered 3 //8/03

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